Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

Features

- Epoxy Meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	V _{CEO}	40 60 80 100	Vdc
Collector-Base Voltage TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	V _{CB}	40 60 80 100	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous	Ic	6.0	Adc
Collector Current - Peak	I _{CM}	10	Adc
Base Current	Ι _Β	2.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	65 0.52	W W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Unclamped Inductive Load Energy (Note 1)	E	62.5	mJ
Operating and Storage Junction, Temperature Range	T _J , T _{stg}	-65 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD - Machine Model	ММ	С	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

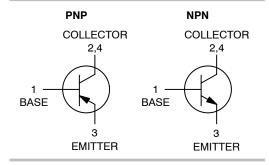
1. I_C = 2.5 A, L = 20 mH, P.R.F. = 10 Hz, V_{CC} = 10 V, R_{BE} = 100 Ω .

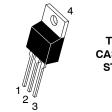


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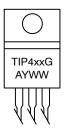
6 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 40-60-80-100 VOLTS, 65 WATTS





TO-220 CASE 221A STYLE 1

MARKING DIAGRAM



TIP4xx = Device Code xx = 1, 1A, 1B, 1C 2, 2A, 2B, 2C A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	1.67	°C/W
Thermal Resistance, Junction-to-Ambient		57	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	,		•	•
Collector-Emitter Sustaining Voltage (Note 2) (I _C = 30 mAdc, I _B = 0) TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	V _{CEO(sus)}	40 60 80 100	- - - -	Vdc
Collector Cutoff Current	I _{CEO}	-	0.7 0.7	mAdc
Collector Cutoff Current $ \begin{aligned} &(V_{CE}=40 \text{ Vdc}, V_{EB}=0) \\ &\text{TIP41G}, \text{TIP42G} \end{aligned} \\ &(V_{CE}=60 \text{ Vdc}, V_{EB}=0) \\ &\text{TIP41AG}, \text{TIP42AG} \end{aligned} \\ &(V_{CE}=80 \text{ Vdc}, V_{EB}=0) \\ &\text{TIP41BG}, \text{TIP42BG} \end{aligned} \\ &(V_{CE}=100 \text{ Vdc}, V_{EB}=0) \\ &\text{TIP41CG}, \text{TIP42CG} \end{aligned}$	I _{CES}	- - -	400 400 400 400	μAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	_	1.0	mAdc
ON CHARACTERISTICS (Note 2)	<u> </u>			
DC Current Gain	h _{FE}	30 15	- 75	-
Collector–Emitter Saturation Voltage (I _C = 6.0 Adc, I _B = 600 mAdc)	V _{CE(sat)}	-	1.5	Vdc
Base-Emitter On Voltage (I _C = 6.0 Adc, V _{CE} = 4.0 Vdc)	V _{BE(on)}	-	2.0	Vdc
DYNAMIC CHARACTERISTICS	<u>'</u>			•
Current–Gain – Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)	f _T	3.0	-	MHz
Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	20	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

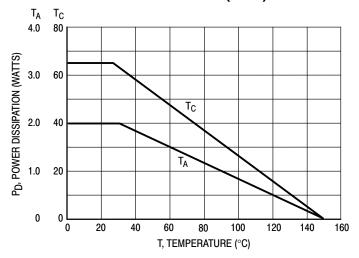
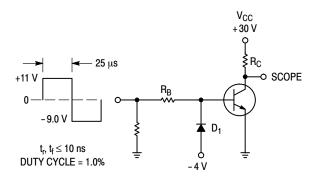


Figure 1. Power Derating



 R_{B} and R_{C} VARIED TO OBTAIN DESIRED CURRENT LEVELS

D₁ MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE I_B \approx 100 mA MSD6100 USED BELOW I_B \approx 100 mA

Figure 2. Switching Time Test Circuit

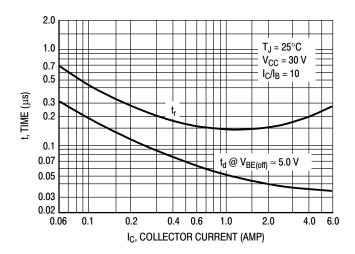


Figure 3. Turn-On Time

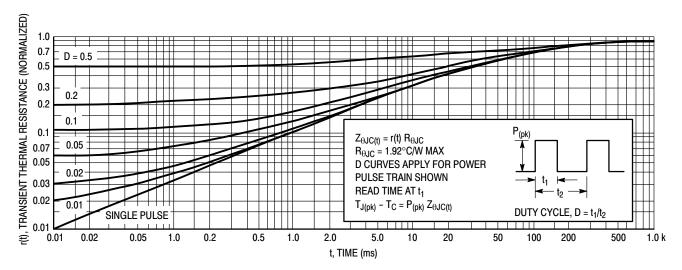


Figure 4. Thermal Response

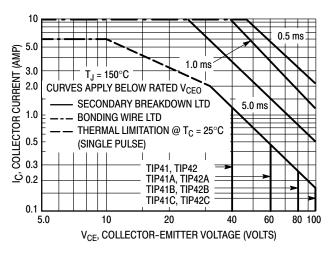


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

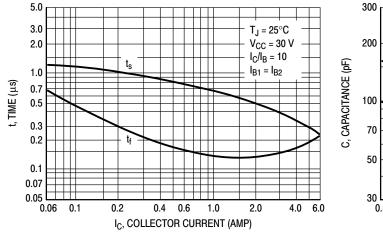


Figure 6. Turn-Off Time

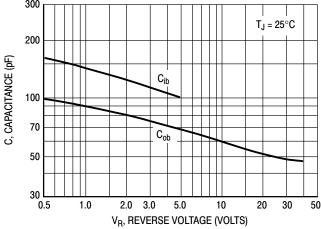


Figure 7. Capacitance

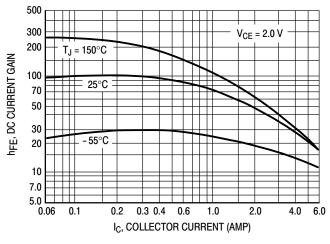


Figure 8. DC Current Gain

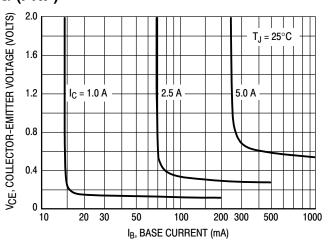


Figure 9. Collector Saturation Region

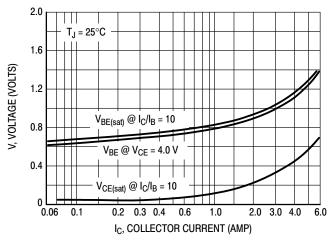


Figure 10. "On" Voltages

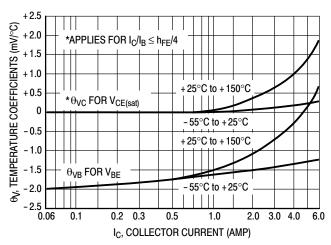


Figure 11. Temperature Coefficients

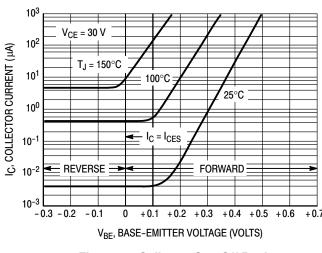


Figure 12. Collector Cut-Off Region

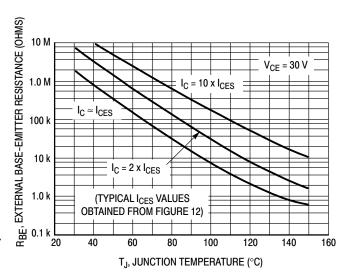
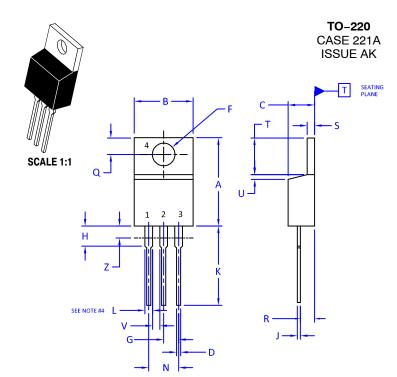


Figure 13. Effects of Base-Emitter Resistance

ORDERING INFORMATION

Device	Package	Shipping
TIP41G	TO-220 (Pb-Free)	50 Units / Rail
TIP41AG	TO-220 (Pb-Free)	50 Units / Rail
TIP41BG	TO-220 (Pb-Free)	50 Units / Rail
TIP41CG	TO-220 (Pb-Free)	50 Units / Rail
TIP42G	TO-220 (Pb-Free)	50 Units / Rail
TIP42AG	TO-220 (Pb-Free)	50 Units / Rail
TIP42BG	TO-220 (Pb-Free)	50 Units / Rail
TIP42CG	TO-220 (Pb-Free)	50 Units / Rail





DATE 13 JAN 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	2. 3.	ANODE CATHODE ANODE CATHODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.		STYLE 10: PIN 1. 2. 3. 4.	GATE	STYLE 11: PIN 1. 2. 3. 4.	DRAIN	STYLE 12: PIN 1. 2. 3. 4.	

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